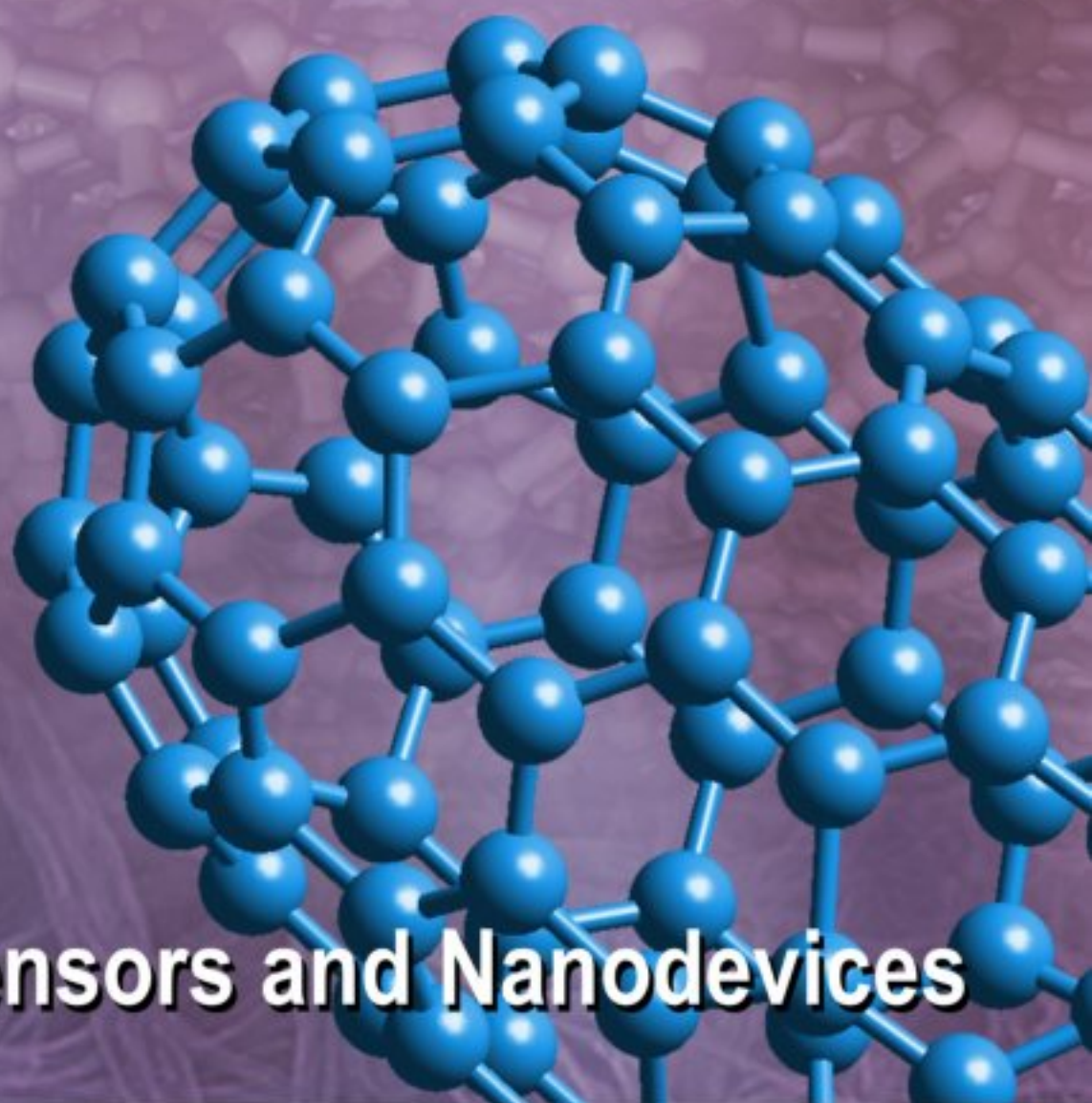


ISSN 1726-5479

# SENSORS & TRANSDUCERS

11<sup>vol. 122</sup>  
/10



## Nanosensors and Nanodevices

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# Contents

Volume 122  
Issue 11  
November 2010

www.sensorsportal.com

ISSN 1726-5479

## Research Articles

<b>New Theoretical Results for High Diffusive Nanosensors Based on ZnO Oxides</b> <i>Paolo Di Sia</i> .....	1
<b>Morphological and Relative Humidity Sensing Properties of Pure ZnO Nanomaterial</b> <i>N. K. Pandey, Karunesh Tiwari</i> .....	9
<b>Humidity Sensing Behaviour of Nanocrystalline <math>\alpha</math>-PbO Synthesized by Alcohol Thermal Process</b> <i>Sk. Khadeer Pasha, L. John Kennedy, J. Judith Vijaya, K. Chidambaram</i> .....	20
<b>Electrochemical Detection of Mn(II) and Cd(II) Mediated by Carbon Nanotubes and Carbon Nanotubes/Li<sup>+</sup> Modified Glassy Carbon Electrode</b> <i>Muhammed M. Radhi, Wee T. Tan, Mohamad Z. AbRahman and Anuar Kassim</i> .....	28
<b>Engineering of Highly Susceptible Paramagnetic Nanostructures of Gd<sub>2</sub>S<sub>3</sub>:Eu<sup>3+</sup>: Potentially an Efficient Material for Room Temperature Gas Sensing Applications</b> <i>Ranu K. Dutta, Prashant K. Sharma and Avinash C. Pandey</i> .....	36
<b>Synthesis and Physical Properties of Nanocomposites (SnO<sub>2</sub>)<sub>x</sub>(In<sub>2</sub>O<sub>3</sub>)<sub>1-x</sub> (x = 0 – 1) for Gas Sensors and Optoelectronics</b> <i>Stanislav Rembeza, Pavel Voronov, Ekaterina Rembeza</i> .....	46
<b>Structural, Electrical Properties of Nanocrystalline Co Doped- La<sub>x</sub>Ce<sub>1-x</sub>O<sub>2</sub> for Gas Sensing Applications</b> <i>A. B. Bodade, Minaz Alvi, N. N. Gedam, H. G. Wankhade and G. N. Chaudhari</i> .....	55
<b>Studies of CNT and Polymer Based Gas Sensor</b> <i>Monika Joshi and R. P Singh</i> .....	66
<b>Excess Noises in (Bio-)Chemical Nanoscale Sensors</b> <i>Ferdinand Gasparyan</i> .....	72
<b>Catechol Biosensor Based on Gold Nanoparticle Modified Tetrabutylammoniumtetrafluoroborate Doped Polythiophene Films</b> <i>Suman Singh, S. Praveen Kumar, D. V. S. Jain, M. L. Singla</i> .....	85
<b>Electromechanical TiO<sub>2</sub> Nanogenerators</b> <i>Valerio Dallacasa, Filippo Dallacasa</i> .....	102
<b>Lead Oxide- PbO Humidity Sensor</b> <i>Sk. KhadeerPasha, K. Chidambaram, L. John Kennedy, J. JudithVijaya</i> .....	113
<b>Ammonia Gas Sensing Properties of Nanocrystalline Zn<sub>1-x</sub>Cu<sub>x</sub>Fe<sub>2</sub>O<sub>4</sub> Doped with Noble Metal</b> <i>S. V. Jagtap, A. V. Kadu, N. N. Gedam and G. N. Chaudhari</i> .....	120

<b>LPG and NH<sub>3</sub> Sensing Properties of SnO<sub>2</sub> Thick Film Resistors Prepared by Screen Printing Technique</b> A. S. Garde.....	128
<b>Effect of Ni Doping on Gas Sensing Performance of ZnO Thick Film Resistor</b> M. K. Deore, V. B. Gaikwad, R. L. Patil, N. K. Pawar, S. D. Shinde, G. H. Jain.....	143
<b>Fabrication and Analysis of Tapered Tip Silicon Microneedles for MEMS based Drug Delivery System</b> Muhammad Waseem Ashraf, Shahzadi Tayyaba, Nitin Afzulpurkar, Asim Nisar.....	158

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## Emerging MEMS 2010

*Technologies & Markets 2010 Report*

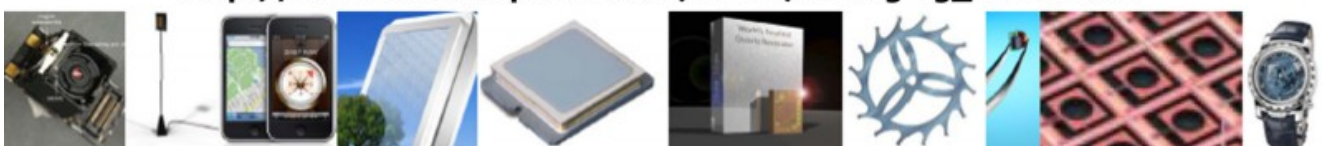
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## ICNS 2011

May 22-27, 2011 - Venice, Italy



**Important deadlines:**

Submission (full paper)	January 10, 2011
Notification	February 20, 2011
Registration	March 5, 2011
Camera ready	March 20, 2011

<http://www.iaria.org/conferences2011/ICNS11.html>

**Tracks:**

- ENCOT: Emerging Network Communications and Technologies
- COMAN: Network Control and Management
- SERVI: Multi-technology service deployment and assurance
- NGNUS: Next Generation Networks and Ubiquitous Services
- MPQSI: Multi Provider QoS/SLA Internetworking
- GRIDNS: Grid Networks and Services
- EDNA: Emergency Services and Disaster Recovery of Networks and Applications
- IPv6DFI: Deploying the Future Infrastructure
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- GOBS: GRID over Optical Burst Switching Networks



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- Advanced biocomputation technologies
- Chemoinformatics
- Bioimaging
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- Biodevices
- Biomedical technologies
- Biological technologies
- Biomanufacturing

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Camera ready	March 20, 2011

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The Sixth International Conference on Systems

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January 23-28, 2011 - St. Maarten,  
The Netherlands Antilles



**Important deadlines:**

Submission (full paper)	September 25, 2010
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- Security and protection systems
- Advanced systems [expert, tutoring, self-adapting, interactive, etc.]
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- Safety in industrial systems
- Complex Systems

## Ammonia Gas Sensing Properties of Nanocrystalline $Zn_{1-x}Cu_xFe_2O_4$ Doped with Noble Metal

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Received: 5 October 2010 /Accepted: 18 November 2010 /Published: 30 November 2010

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**Abstract:** The sensors are required basically for monitoring of trace gases in environment. In order to detect, measure and control these gases; one should know the amount and type of gases present in the environment. Among the most toxic and hazardous gases, it is necessary to detect and monitor the ammonia gas because this is enhance in the agricultural sector by the addition of large amounts of  $NH_3$  to cultivated farmland in the form of fertilizers. Nanocrystalline spinel type  $Zn_{1-x}Cu_xFe_2O_4$  ( $x=0, 0.2, 0.4, 0.6$  &  $0.8$ ) has been synthesized by sol-gel citrate method. The synthesized powders were characterized by XRD and SEM. The results revealed that the particle size is in the range of 40–45 nm for Cu–Zn ferrite with good crystallinity. The gas sensing properties were studied towards reducing gases like CO, LPG,  $NH_3$  and  $H_2S$  and it is observed that Cu–Zn ferrite shows high response to ammonia gas at relatively lower operating temperature. The  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  nanomaterial shows better sensitivity towards  $NH_3$  gas at an operating temperature  $300^\circ C$ . Incorporation of Pd improved the sensitivity, selectivity, response time and reduced the operating temperature from  $300^\circ C$  to  $250^\circ C$  for  $NH_3$  sensor. Copyright © 2010 IFSA.

**Keywords:**  $NH_3$  sensor, Cu–Zn ferrite, Sensitivity, Selectivity, Palladium.

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### 1. Introduction

The increasing concern over environmental monitoring and safety demand in industry and home has generated great interest in developing gas sensors [1]. A large number of metal oxides, i.e.  $SnO_2$ ,  $ZnO$ ,  $WO_3$ ,  $TiO_2$ ,  $Fe_2O_3$  and mixed oxides, were reported to be sensitive to certain gas species. Now-a-days, the atmospheric pollution has become a global issue. The gases from auto and industrial exhausts are polluting the environment. The need to detect, measure and control these gases has led to the research and development of a wide variety of sensors using different materials and techniques.

Recently, the need of ammonia sensor has greatly increased in many fields of technological importance, such as food technology, chemical engineering, medical diagnosis, environmental protection, monitoring of car interiors and industrial processes [2]. Semiconductor metal oxide chemical sensors have shown advantages in commercialization prospect and market potential. These advantages include long lifetime, fast response and recovery time, low cost, simple electronic structure, and low maintenance [3]. Hence, the metal oxide gas-sensing materials have been widely investigated for a long time [4–6]. Recently, some composite oxides such as spinel [7] and perovskite [8] were found to be more attractive than single-metal oxides for their better selectivity and/or sensitivity to certain gases. Spinel-type oxides with a general formula of  $AB_2O_4$  are important mixed oxides in gas sensors, and have been investigated for the detection of both oxidizing and reducing gases.

Other earlier reports about the application study of  $ZnFe_2O_4$  as a gas sensing material include  $ZnFe_2O_4$  particles to  $H_2S$  [9], a directly deposited film to CO [10], ultrafine powder to  $Cl_2$  [11], CdO-doped  $ZnFe_2O_4$  to ethanol [12], a  $ZnO/ZnFe_2O_4$  thick film to propanol [13]. Duan *et al.* [14–16] have designed a novel synthetic route of pure  $MFe_2O_4$  ( $M = Mg, Co, \text{ and } Ni$ ) spinel ferrites using a single molecular precursor.

In present work, the Cu doped  $ZnFe_2O_4$  nanopowders were synthesized by sol-gel citrate method. The  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  shows high sensing response to ammonia at an operating temperature  $300\text{ }^\circ\text{C}$  and negligible sensing response to other test gases like LPG, CO and  $H_2S$ . Dispersion of noble metal such as Pd further enhanced the sensing response and reduced the operating temperature up to  $250\text{ }^\circ\text{C}$  for ammonia gas. The structural and microstructural characteristics of  $ZnFe_2O_4$  have been carried out with the help of XRD and SEM.

## **2. Experimental Details**

### **2.1. Material Synthesis**

The  $Zn_{1-x}Cu_xFe_2O_4$  ( $x=0.2, 0.4, 0.6$  and  $0.8$ ) were synthesized by sol-gel method using ethylene glycol as a solvent. All reagents were of analytical grade were used. Firstly, the analytically pure grade  $[Fe(NO_3)_3 \cdot 9H_2O]$ ,  $[Zn(NO_3)_2 \cdot 6H_2O]$ ,  $[Cu(NO_3)_2 \cdot 3H_2O]$  and citric acid were weighed and dissolved in ion-free water at  $80\text{ }^\circ\text{C}$  for 2 h. Then ethylene glycol was added under constant stirring to obtain a homogeneous and stable sol. The solution was further heated in pressure vessel at about  $130\text{ }^\circ\text{C}$  for 12 h. During this reaction transparent solution was transform into a gel state with very high viscosity. The material was then heated in a furnace at  $350\text{ }^\circ\text{C}$  for 3 h and a violent combustion was occurs which spontaneously propagates until all the gel was burnt out to form a loose powder. The powder was then calcined at  $650\text{ }^\circ\text{C}$  for 6 h in order to improve the crystallinity of materials. Samples of resulting  $Zn_{1-x}Cu_xFe_2O_4$  with varied weight percentage of Pd were prepared by the impregnation technique.

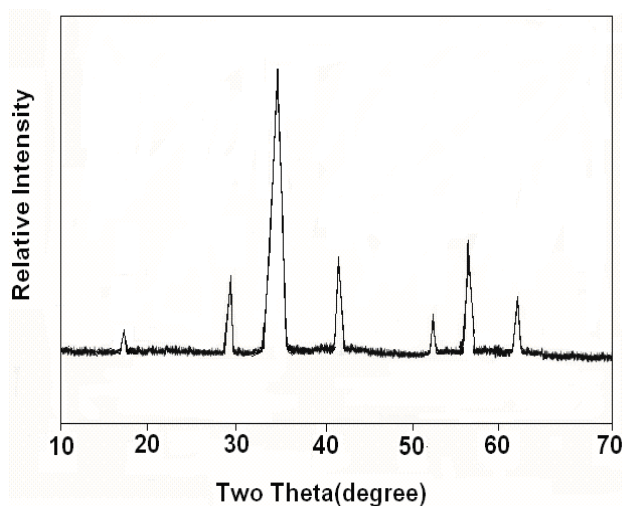
### **2.2. Characterization of Samples**

The synthesized samples were characterized by powder X-ray diffraction (XRD) using a Siemens D 5000 diffractometer. The XRD data were recorded by using  $Cu\ K\alpha$  radiation ( $1.5406\text{ \AA}$ ). The intensity data were collected over a  $2\theta$  range of  $10\text{--}70\text{ }^\circ$ . The average crystallite size of the samples was estimated with the help of Scherrer equation using the diffraction intensity of all prominent lines. The microstructure of the materials was evaluated by scanning electron microscopy (SEM).

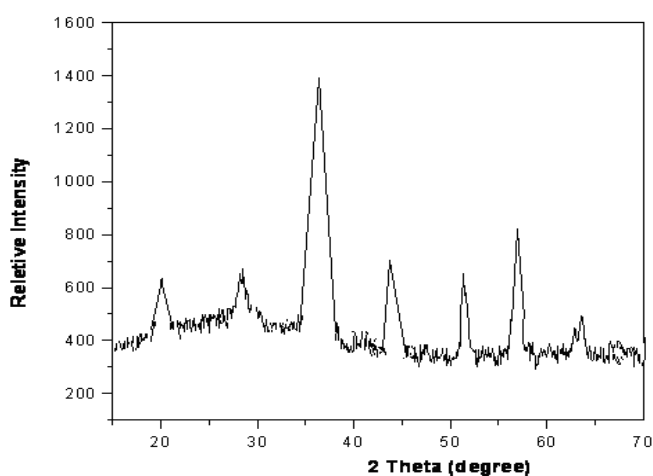
### 3. Results and Discussion

#### 3.1. X-ray Diffraction Study

The XRD patterns of the compositions  $\text{ZnFe}_2\text{O}_4$  and  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  prepared by sol-gel citrate method calcined at  $650\text{ }^\circ\text{C}$  are presented in Fig. 1. Fig. 1 (a), shows the XRD pattern, which is in good agreement with XRD results previously reported in the literature for  $\text{ZnFe}_2\text{O}_4$  [17]. Further confirmation of this result was found using the JCPDS card No: 77-0011 [18]. The diffraction lines are found to be sharp and no other phase has been detected for all the samples, which are consistent with face centered cubic spinel structure. Fig. 1 (b), shows the XRD pattern of  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  nanomaterial, which is a spinel- type oxide [19]. The XRD peaks correspond to the cubic structure of the spinel ferrite and no other peaks observed are indicating the absence of any other phase or impurities. Extremely broad reflections are observed indicating nanosized particle nature of the material obtained. The average particle size of the nanocrystalline  $\text{ZnFe}_2\text{O}_4$  and  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  according to the scherrer formula were in the range of 40–45 nm.



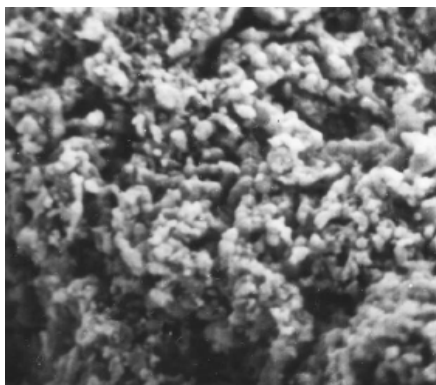
**Fig. 1 (a).** X-ray pattern of  $\text{ZnFe}_2\text{O}_4$  calcined at  $650\text{ }^\circ\text{C}$ .



**Fig. 1 (b).** X-ray pattern of  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  calcined at  $650\text{ }^\circ\text{C}$ .

### 3.2. SEM analysis

The microstructure of the samples can be visualized from scanning electron micrograph of the synthesized material as in Fig. 2. One can notice the presence of irregular-shaped aggregates is formed by aggregation of very fine particles. Many large and small pores are present in the whole material. We assumed that the pores are mainly intergranular because intragranular pores are not observed on the SEM photograph.



**Fig. 2.** SEM micrograph of Zn<sub>0.6</sub>Cu<sub>0.4</sub>Fe<sub>2</sub>O<sub>4</sub> calcined at 650 °C.

### 3.3. Gas Sensing Properties

#### 3.3.1. Fabrication and Analysis of Gas Sensors

The prepared powders were mixed with PVA (polyvinyl alcohol) to form paste, and then the paste was coated onto an Al<sub>2</sub>O<sub>3</sub> tube on which two platinum wires had been installed at each end. A small Ni–Cr alloy coil was placed through the tube as a heater, which provided operating temperature at 50–350 °C. The temperature was controlled by adjusting the heating power. Gas response is defined as the ratio of change in resistance of the sample on exposure to a test gas to the resistance in the presence of air.

$$S = (R_a - R_g)/R_a = \Delta R/R_a, \quad (1)$$

where  $R_a$  is the resistance in air,  $R_g$  the resistance in a sample gas, and  $\Delta R$  the change in resistance. The gas sensing properties of reducing gases such as LPG, H<sub>2</sub>S, CO and NH<sub>3</sub> were measured. The test temperature range is from 50-300 °C and the gas concentration tested for 350 ppm.

#### 3.3.2. Sensitivity of Zn<sub>1-x</sub>Cu<sub>x</sub>Fe<sub>2</sub>O<sub>4</sub>

Fig. 3. shows the response as a function of operating temperatures for undoped ZnFe<sub>2</sub>O<sub>4</sub> nanopowder calcined at 650 °C for 6 h for NH<sub>3</sub> gas. The sensor element shows the high response 0.22 towards NH<sub>3</sub> at an operating temperature 300 °C. In order to promote gas response, dopants are shown to effectively influence the semiconductive properties of sensor materials. For the mixed ferrites such as Zn<sub>1-x</sub>Cu<sub>x</sub>Fe<sub>2</sub>O<sub>4</sub> (x=0.2 to 0.8), the gas sensitivity depends on the operating temperature and Cu content. The sensitivity increases with increasing temperature and reaches a maximum value corresponding to an optimum operating temperature. For the Zn<sub>0.8</sub>Cu<sub>0.2</sub>Fe<sub>2</sub>O<sub>4</sub> sample, there is a slow increase in the sensitivity to the maximum value of 0.44 at optimum operating temperature of 300 °C, whereas for Zn<sub>0.6</sub>Cu<sub>0.4</sub>Fe<sub>2</sub>O<sub>4</sub> sample, the sensitivity to the maximum value of 0.75 at 300 °C, then sensitivity decreases. Compared with other samples, Zn<sub>0.6</sub>Cu<sub>0.4</sub>Fe<sub>2</sub>O<sub>4</sub> showed the large response to NH<sub>3</sub>. The

reason may be that the partial replacement of Zn ions by Cu ions at the A-sites is advantageous to adsorption by creating active sites and oxidation for  $\text{NH}_3$ . In addition, the partial replacement results in a decrease of grain size and hence in an increase of surface area. Since small grains have relatively large grain boundary areas, the adsorption of  $\text{NH}_3$  molecules is relatively high.

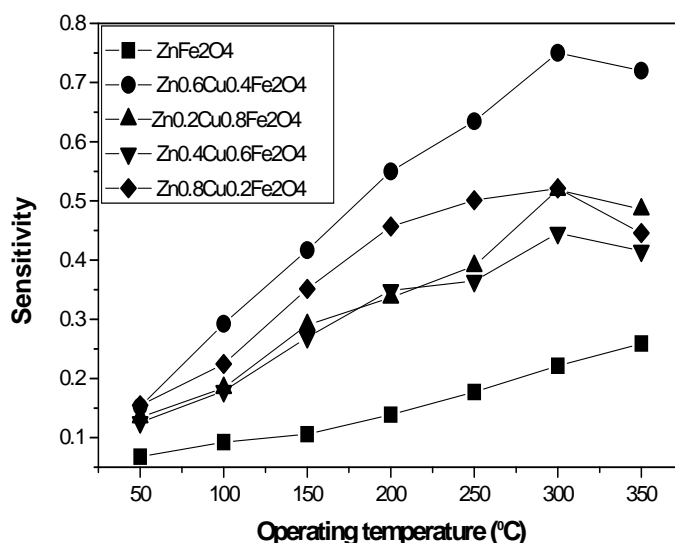


Fig. 3. Sensitivity vs. operating temperature for studied samples calcined at 650°C for  $\text{NH}_3$  gas.

### 3.3.3. Selectivity Test

The sensitivity of the sample  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  was also investigated for different reducing gases such as LPG,  $\text{NH}_3$ ,  $\text{H}_2\text{S}$  and CO at different operating temperatures. Fig. 4, shows the sensitivity of the  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  sample to various test gases as a function of operating temperature. It is seen that the sensor exhibits high sensitivity to  $\text{NH}_3$  gas at an operating temperature of 300 °C and other reducing gases like LPG,  $\text{H}_2\text{S}$  and CO shows less response.

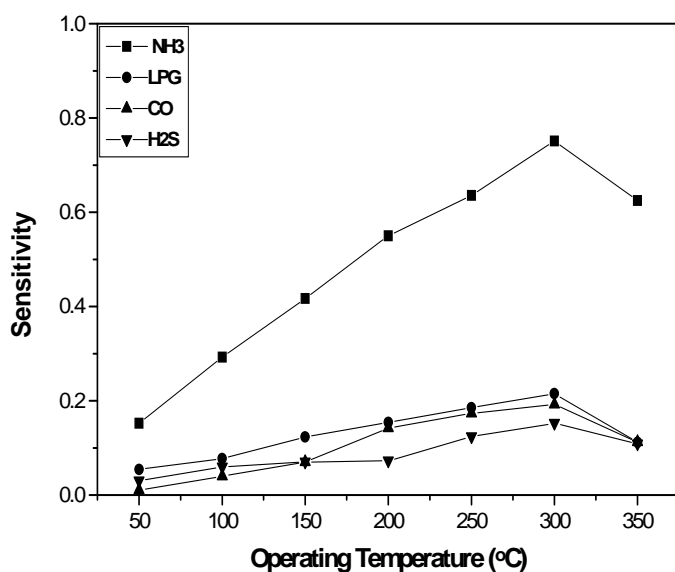
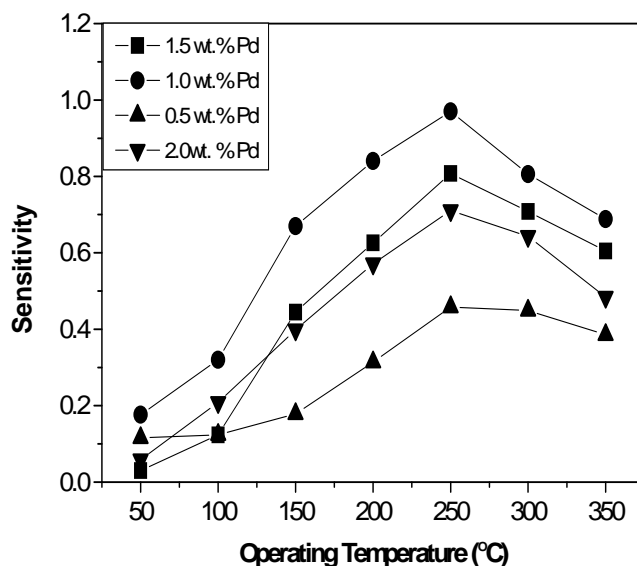


Fig. 4. Sensitivity vs. operating temperature of  $\text{Zn}_{0.6}\text{Cu}_{0.4}\text{Fe}_2\text{O}_4$  calcined at 650 °C for various reducing gases.

### 3.3.4. Sensing behavior of Pd Loaded

In order to improve the response, Pd was incorporated to  $Zn_{0.6}Cu_{0.4}Fe_2O_4$ . Pd is proved to be highly effective in improving the sensitivity of semiconducting oxides for reducing gases [20]. The Pd is known to have a catalytic effect due to its excellent oxidation capability [21]. Fig. 5, shows sensitivity versus operating temperature of different wt. % Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$ . It is evident from the figure that 1.0 wt.% Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  shows the maximum sensitivity and then further increase in Pd concentration, sensitivity decreased drastically towards  $NH_3$  gas, that suggests the importance of the dispersion of Pd on the semiconductor surface [22]. The incorporation of Pd results in a drastic decrease in the operating temperature for maximum response for  $NH_3$  from 300 to 250 °C.



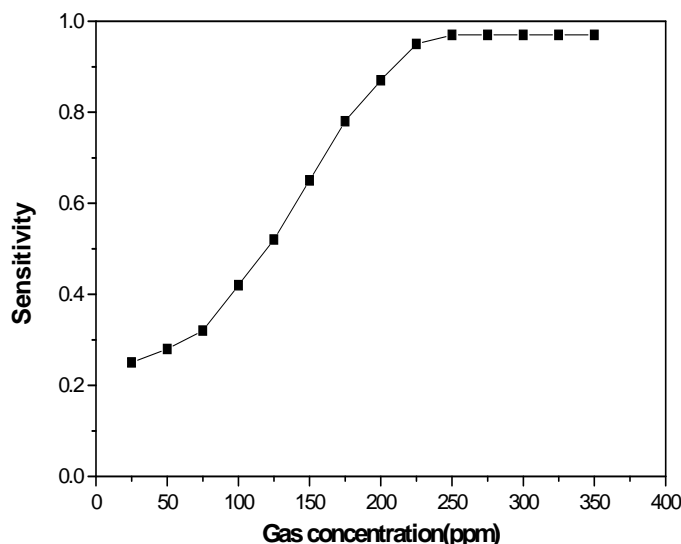
**Fig. 5.** Sensitivity vs. operating temperature with different concentration of Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  calcined at 650 °C for  $NH_3$  gas sensor.

### 3.3.5. Effect of Concentration on Gas Sensitivity

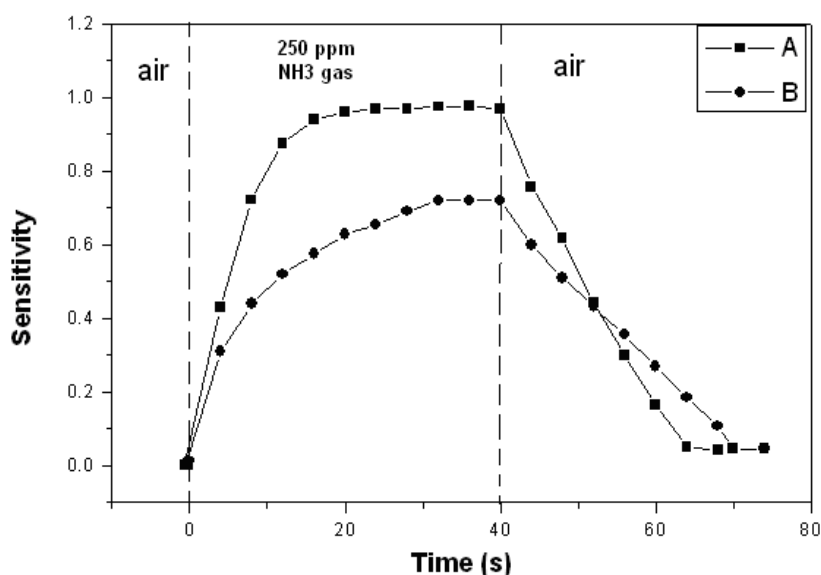
The sensitivity with the  $NH_3$  gas concentration of the 1.0 wt. % Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  calcined at an operating temperature 650 °C as shown in Fig. 6. It is observed that the sensitivity increases linearly up to 250 ppm of  $NH_3$  gas concentration and after that it saturates. The response of a sensor depends on removal of adsorbed oxygen molecules by reaction with a target gas and generation of electrons. For a small concentration of gas, exposed on a fixed surface area of a sample, there is a lower coverage of gas molecules on the surface and hence lower surface reaction occurred. An increase in gas concentration increases the surface reaction due to a larger surface coverage. A further increase in surface reaction will be gradual when the saturation point on the coverage of molecules is reached. After 250 ppm level of  $NH_3$  gas the curve flattens because there would not be enough ionosorbed oxygen species to contribute to detecting mechanisms. The linear behavior of the curve may be extended to some extent by taking longer area of the sensor.

### 3.3.6. Response and Recovery of the Sensor

Fig. 7 shows the response characteristics for the  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  at 300 °C and 1.0 wt. % Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  at 250 °C to 250 ppm  $NH_3$  gas. The 1.0 wt. % Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  sensor exhibits shorter response and recovery times (10 and 25 s respectively) than pure  $Zn_{0.6}Cu_{0.4}Fe_2O_4$ .



**Fig. 6.** Sensitivity to ethanol gas concentration for 1.0 wt. % Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  calcined at  $650\text{ }^{\circ}C$ .



**Fig. 7.** The response and recovery characteristics to 250 ppm  $NH_3$  gas for (A) 1.0 wt. % Pd doped  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  and (B)  $Zn_{0.6}Cu_{0.4}Fe_2O_4$

#### 4. Concussion

Nanocrystalline Cu–Zn ferrite has been synthesized by a convenient sol–gel citrate route. The XRD pattern of  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  shows spinel structure. The results revealed that the particle size is in the range of 40–45 nm for  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  with good crystallinity. The  $Zn_{0.6}Cu_{0.4}Fe_2O_4$  sensor shows excellent sensing characteristics towards  $NH_3$  gas at operating temperature  $300\text{ }^{\circ}C$ . The 1.0 wt% Pd incorporation lowers the operating temperature from 300 to  $250\text{ }^{\circ}C$  and exhibited the highest response value, excellent selectivity and quick response behavior to  $NH_3$  gas. The sensor is very promising for  $NH_3$  detection in the range 0-250 ppm with a response time in second range.

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- SEMOSN: Security and monitoring of sensor networks
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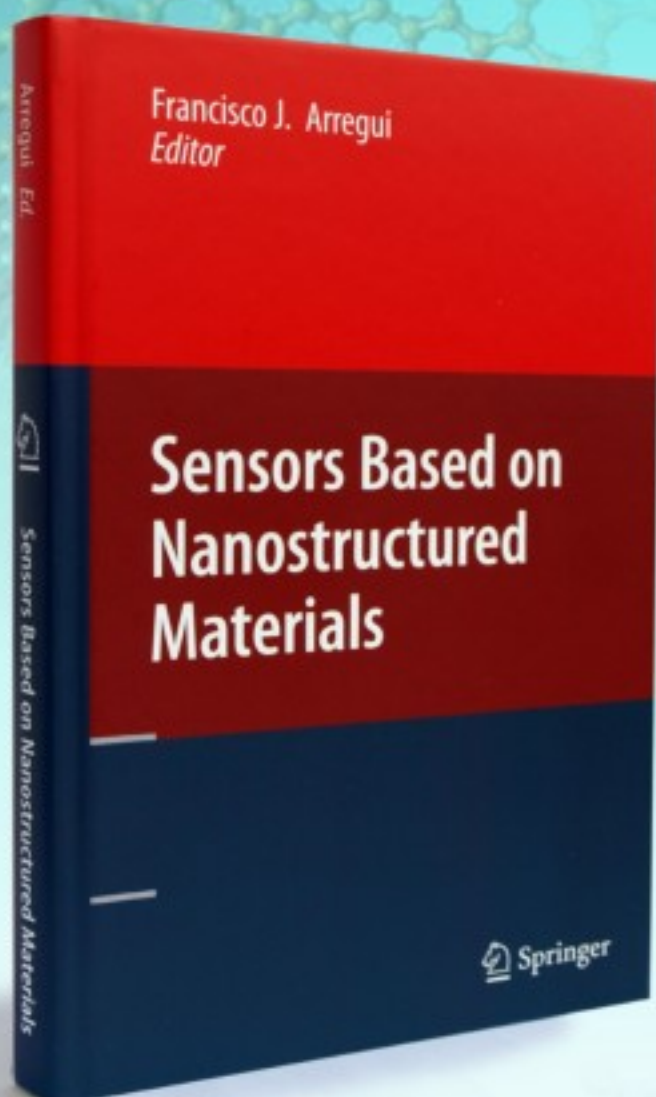
- Physical, chemical and biosensors;
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- Smart sensors and systems;
- Sensor instrumentation;
- Virtual instruments;
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